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RFMD(R) Unveils Complete Front End Module for Handheld WiFi and Bluetooth(R) Systems

GREENSBORO, N.C., May 13, 2010 (GlobeNewswire via COMTEX News Network) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance RF components and compound semiconductor technologies, today unveiled a highly integrated new front end module (FEM) that delivers a complete integrated solution for handset/handheld WiFi 802.11b/g/n and Bluetooth(R) systems.

RFMD's RF5755 FEM integrates a 2.5GHz Power Amplifier (PA), multi-throw switch (SP3T), Low Noise Amplifier (LNA) and power detector coupler. The RF5755 also features integrated matching circuitry with output harmonic attenuation, reducing the bill of materials (BOM) and manufacturing costs. The RF5755 is packaged in a small 16-pin QFN package (3mm x 3mm x 0.5mm), minimizing layout area in customer applications.

The highly integrated RF5755 delivers many features and customer benefits: high linear output power (20dBm) allowing higher efficiency and lower EVM for 11n applications; the ability to switch between WiFi transmit, WiFi receive, or Bluetooth (transmit or receive); reduced need for a high loss/attenuation filter at the FEM output; high IIP3 and gain; simultaneous receive of WiFi and Bluetooth with positive gain in both paths (utilizing the SPST switch after the LNA); and a direct-to-battery connection eliminating the need for additional DC circuitry. Additionally, the integrated power detector coupler decreases sensitivity to voltage supply, temperature, and VSWR and improves the accuracy of the closed loop power control.

The RF5755 FEM is fully tested, including EVM and all DC parameters, providing a reduced size, single-placement solution that minimizes system footprint, reduces costs, and accelerates time-to-market for high linear output power applications.

About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

The RF Micro Devices, Inc. logo is available at http://www.globenewswire.com/newsroom/prs/?pkgid=6436

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including risks associated with the impact of global macroeconomic and credit conditions on our business and the business of our suppliers and customers, variability in operating results, the rate of growth and development of wireless markets, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication, molecular beam epitaxy, assembly and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to bring new products to market, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on a limited number of customers, dependence on gallium arsenide (GaAs) for the majority of our products, and dependence on third

parties. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

SOURCE: RF Micro Devices

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